UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO. : 6,896,969 B2 Page 1 of 2

DATED : May 24, 2005 INVENTOR(S) : Alan R. Reinberg

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 2,

Lines 31 and 32, reads "low temperatures (i.e., approximately 400° C. and is therefore not damaging to the underlying polysilicon conductive" should read -- low temperatures (i.e., approximately 400° C and is therefore not damaging to the underlying polysilicon conductive --.

Column 4,

Line 4, reads "a temperature ranging from 100° to 600° C. at a pressure" should read -- a temperature ranging from 100° to 600° C at a pressure --.

Column 5,

Line 37, reads " V_2O_3 , V_2O_5 , VO_2 , V_2O_5 , VO_2 , VO_3 , V_2O_3 , VO_3

Column 8,

Line 15, reads "point of 16.8° C. (62.2° F.). A small amount of inhibitor" should read -- point of 16.8° C (62.2° F). A small amount of inhibitor --.

Line 18, reads "higher melting beta- (m.p. 32.5° C.) and alpha- (m.p." should read -- higher melting beta- (m.p. 32.5° C) and alpha- (m.p. --.

Line 19, reads "62.3° C. forms of sulfur trioxide. Gamma-form sulfur" should read -- 62.3° C forms of sulfur trioxide. Gamma-form sulfur --.

Line 22, reads "has a melting point of greater than 16.8° C., the sulfur" should read -- has a melting point of greater than 16.8° C, the sulfur --.

Column 9,

Line 34, reads "between 100° C. to 600° C.; and the time of exposure, given" should read -- between 100° C to 600° C; and the time of exposure, given --.

Column 11,

Line 63, reads "600° C. and the sulfur trioxide is preferably in contact with" should read -- 600° C and the sulfur trioxide is preferably in contact with --.

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Page 2 of 2

DATED : May 24, 2005 INVENTOR(S) : Alan R. Reinberg

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 12,

Line 53, reads " V_2O_5 , VO_2 and ZnO" should read -- VaO_5 , VO_2 , and ZnO --. Line 63, reads "comprised of substoichemetric tantalum oxide." should read -- comprised of substoichiometric tantalum oxide. --.

Line 67, reads "comprised of substoichemetric oxide." should read -- comprised of substoichiometric oxide. --.

Column 13,

Line 4, reads "temperature ranging from 100° C. to 600° C." should read -- temperature ranging from 100° C to 600° C. --.

Column 14,

Lines 5 and 6, reads "is comprised of substoichemetric tantalum oxide layer having a thickness of 5 to 200 Angstroms, wherein the sulfur" should read -- is comprised of substoichiometric tantalum oxide layer having a thickness of 5 to 200 Angstroms, wherein the sulfur --.

Lines 7 and 8, reads "trioxide is gaseous sulfur trioxide, wherein the substoichemetric tantalum oxide layer is disposed on a conductive" should read -- trioxide is gaseous sulfur trioxide, wherein the substoichiometric tantalum oxide layer is disposed on a conductive --.

Signed and Sealed this

Twenty-eighth Day of March, 2006

JON W. DUDAS
Director of the United States Patent and Trademark Office